

AMENDMENTS TO THE CLAIMS

Please amend the claims as follows:

1. (Currently amended) An electromagnetic wave shielding material which comprises a transparent substrate and a fine line pattern formed thereon,
wherein the fine line pattern comprises a metal plating film using a plated upon physically developed metal silver as a catalytic nucleus nuclei deposited on the substrate.
2. (Original) The electromagnetic wave shielding material according to Claim 1, wherein the fine line pattern has a thickness of 15 μm or less and a line width of 40 μm or less, a total luminous transmittance of 50% or higher, and a surface resistance of 10 ohm/ \square or less.
3. (Previously presented) The electromagnetic wave shielding material according to Claim 2, wherein the total luminous transmittance is 60% or higher.
4. (Previously presented) The electromagnetic wave shielding material according to Claim 2, wherein the surface resistance is 7 ohm/ \square or less.
5. (Previously presented) The electromagnetic wave shielding material according to Claim 2, wherein the thickness of the fine line pattern is 0.5 to 15 μm .
6. (Previously presented) The electromagnetic wave shielding material according to Claim 5, wherein the thickness of the fine line pattern is 2 to 12 μm .
7. (Previously presented) The electromagnetic wave shielding material according to Claim 2, wherein the line width of the fine line pattern is 1 to 40 μm .
8. (Previously presented) The electromagnetic wave shielding material according to Claim 1, wherein the plating is an electrolytic plating.

9. (Previously presented) The electromagnetic wave shielding material according to Claim 1, wherein the plating is at least one kind of plating selected from copper and nickel.

10. (Currently amended) A process for preparing an electromagnetic wave shielding material which comprises in order the steps of:

a) exposing a light-sensitive material having a physical development nuclei layer and a silver halide emulsion layer on a transparent substrate in this order with an optional fine line pattern,

b) precipitating metal silver with an~~the~~ optional fine line pattern onto the physical development nuclei layer by physical development, then,

c) removing a~~any~~ layer provided on the physical development nuclei layer, and

d) subjecting to plating a metal ~~with the use of~~ onto the physically developed metal silver as a catalytic nucleus nuclei.

11. (Original) The process for preparing an electromagnetic wave shielding material according to Claim 10, wherein the fine line pattern has a thickness of 15 μm or less and a line width of 40 μm or less, a total luminous transmittance of 50% or higher, and a surface resistance of 10 ohm/ \square or less.

12. (Previously presented) The process for preparing an electromagnetic wave shielding material according to Claim 11, wherein the total luminous transmittance is 60% or higher.

13. (Previously presented) The process for preparing an electromagnetic wave shielding material according to Claim 11, wherein the surface resistance is 7 ohm/ \square or less.

14. (Previously presented) The process for preparing an electromagnetic wave shielding material according to Claim 11, wherein the thickness of the fine line pattern is 0.5 to 15 μm .

15. (Previously presented) The process for preparing an electromagnetic wave shielding material according to Claim 14, wherein the thickness of the fine line pattern is 2 to 12 μm .

16. (Previously presented) The process for preparing an electromagnetic wave shielding material according to Claim 11, wherein the line width of the fine line pattern is 1 to 40 μm .

17. (Previously presented) The process for preparing an electromagnetic wave shielding material according to Claim 10, wherein the plating is an electrolytic plating.

18. (Previously presented) The process for preparing an electromagnetic wave shielding material according to Claim 10, wherein the plating is at least one kind of plating selected from copper and nickel.

19. (Previously presented) The process for preparing an electromagnetic wave shielding material according to Claim 18, wherein an electrolytic plating is carried out by dipping a transparent substrate on which a physically developed silver has been formed in a bath containing copper sulfate and sulfuric acid as main components with a current density of 1 to 20 ampere/dm² at 10 to 40°C.